L Number	Hits	Search Text	DB	Time stamp
6	21	base with (eliminate remov\$3) near (hydrogen "h.sub.2")	USPAT;	2003/10/13 13:09
1.3		and (438/\$6 257/\$6)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
7	13	(US-5846869-\$ or US-6031255-\$ or US-6258685-\$ or	USPAT;	2003/10/13 13:09
'		US-6432788-\$ or US-6451659-\$ or US-6455390-\$ or	US-PGPUB	_ · · ·
		US-6537838-\$ or US-4047976-\$ or US-5693541-\$).did. or		
		(US-20010026971-\$ or US-20020031892-\$ or		
		US-20020058399-\$ or US-20020187568-\$).did.		
8	8	( base with (eliminate remov\$3) near (hydrogen "h.sub.2")	USPAT;	2003/10/13 13:10
		and (438/\$6 257/\$6)) not ((US-5846869-\$ or US-6031255-\$	US-PGPUB;	• •
		or US-6258685-\$ or US-6432788-\$ or US-6451659-\$ or	EPO; JPO;	
		US-6455390-\$ or US-6537838-\$ or US-4047976-\$ or	DERWENT;	
		US-5693541-\$).did. or (US-20010026971-\$ or	IBM_TDB	
		US-20020031892-\$ or US-20020058399-\$ or	_	
		US-20020187568-\$).did.)		
-	158	((heterojunction hetero) with (bipolar bi near polar) with	USPAT;	2003/10/10 09:56
		(transistor) hbt hbts) and base and emitter with mesa and	US-PGPUB;	, ,
		base with (contact and electrode)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1649	(438/47,94,172,191,235,312,313,314,315,317,320,for.286).C		2003/10/10 11:18
	20.5	(100) 11/0 1/2/2/2017=00/00=/00=/00=/00=/00=/00=/00=/00=/00=	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	52	(((heterojunction hetero) with (bipolar bi near polar) with	USPAT;	2003/10/10 10:57
		(transistor) hbt hbts) and base and emitter with mesa and	US-PGPUB;	, ,
]		base with (contact and electrode)) and	EPO; JPO;	
		((438/47,94,172,191,235,312,313,314,315,317,320,for.286).		
		((,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	IBM_TDB	
-	,2	("6399971").PN.	USPAT;	2003/10/10 10:40
	,-		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	6399971.URPN.	USPAT	2003/10/10 10:38
-	1	"5481120".PN.	USPAT	2003/10/10 10:38
-   i	2	jp-05326546-\$.did.	USPAT;	2003/10/10 10:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	jp-08-335588-\$.did.	USPAT;	2003/10/10 10:41
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	jp-05326546-\$.did. jp-08335588-\$.did. jp-07015357-\$.did.	JPO	2003/10/10 10:41
-	1	jp-08335588-\$.did.	USPAT;	2003/10/10 10:42
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	jp-07015357-\$.did.	USPAT;	2003/10/10 10:43
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

	· · · · · · · · · · · · · · · · · · ·			2002/40/40 40 40
-	0	jp-0715357-\$.did.	USPAT;	2003/10/10 10:43
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	jp-70015357-\$.did.	USPAT;	2003/10/10 10:56
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	482	(carbon c) near4 (dope doping doped) with base	USPAT;	2003/10/10 11:12
			US-PGPUB;	
			EPO; JPO;	
	]		DERWENT;	ı
			IBM_TDB	
_	11	(((heterojunction hetero) with (bipolar bi near polar) with	USPAT;	2003/10/10 11:41
	**	(transistor) hbt hbts) and base and emitter with mesa and	US-PGPUB;	
		base with (contact and electrode)) and	EPO; JPO;	
		((438/47,94,172,191,235,312,313,314,315,317,320,for.286).		
		and ((carbon c) near4 (dope doping doped) with base)	IBM_TDB	
	745	(carbon c) near4 (dope doping doped implant\$5) with base	USPAT;	2003/10/10 11:09
-	745	(carbon c) heart (dope doping doped implants) with base	US-PGPUB;	2003/10/10 11.03
			EPO; JPO;	
		·		
			DERWENT;	
ļ		( ) A ( ) and desire desired involved by the book	IBM_TDB	2002/10/10 11:12
-	745	(carbon c) near4 (dope doping doped implant\$5) with base	USPAT;	2003/10/10 11:12
			US-PGPUB;	
			EPO; JPO;	
Į			DERWENT;	
			IBM_TDB	000044044044
-	12	(((heterojunction hetero) with (bipolar bi near polar) with	USPAT;	2003/10/10 11:12
		(transistor) hbt hbts) and base and emitter with mesa and	US-PGPUB;	
		base with (contact and electrode)) and	EPO; JPO;	
		((438/47,94,172,191,235,312,313,314,315,317,320,for.286).(	CODER,WENT;	
		and ((carbon c) near4 (dope doping doped implant\$5) with	IBM_TDB	_
-	1	tasheterojunction hetero) with (bipolar bi near polar) with	USPAT;	2003/10/10 11:13
		(transistor) hbt hbts) and base and emitter with mesa and	US-PGPUB;	
		base with (contact and electrode)) and	EPO; JPO;	
		((438/47,94,172,191,235,312,313,314,315,317,320,for.286).	COLER/WENT;	
1		and ((carbon c) near4 (dope doping doped implant\$5) with	IBM_TDB	
	1	base)) not ((((heterojunction hetero) with (bipolar bi near		
		polar) with (transistor) hbt hbts) and base and emitter with		
		mesa and base with (contact and electrode)) and		
		((438/47,94,172,191,235,312,313,314,315,317,320,for.286).	CLS.)	
	1	and ((carbon c) near4 (dope doping doped) with base))		
-	1649	(438/47,94,172,191,235,312,313,314,315,317,320,for.286).C	CLESPAT;	2003/10/13 12:07
			US-PGPUB;	
			EPO; JPO;	
-			DERWENT;	
		,	IBM_TDB	
_	1238129	(gallium indium ga in) with (arsenic antimony as sb)	USPAT;	2003/10/10 11:29
		(gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as	US-PGPUB;	' '
		sb" "in ga sb as" "ga in sb as" gaassb gasbas "ga as sb" "ga	EPO; JPO;	
	1	sb as" inassb insbas "in as sb" "in sb as" gainas gainsb	DERWENT;	
		ingaas ingasb "ga in as" "ga in sb" "in ga as" "in ga sb") and	IBM_TDB	
		((438/47,94,172,191,235,312,313,314,315,317,320,for.286).		
1_	1003	((gallium indium ga in) with (arsenic antimony as sb)	USPAT;	2003/10/10 11:35
1-	1003	(gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as	US-PGPUB;	
		sb" "in ga sb as" "ga in sb as" gaassb gasbas "ga as sb" "ga	EPO; JPO;	
		sb as" inassb insbas "in as sb" "in sb as" gainas gainsb	DERWENT;	
	-	ingaas ingasb "ga in as" "ga in sb" "in ga as" "in ga sb")) and	IBM_TDB	
		((438/47,94,172,191,235,312,313,314,315,317,320,for.286).		
	I	((TU)  117' 117' 117' 116' 116' 117' 117' 11' 11' 11' 11' 11' 11' 11'		L

-	1002	((gallium indium ga in) with (arsenic antimony as sb)	USPAT;	2003/10/10 11:37
		(gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb	US-PGPUB; EPO; JPO;	
1		as" gainas ingaas "ga in as" "in ga as")) and	DERWENT;	
		((438/47,94,172,191,235,312,313,314,315,317,320,for.286).0		
-	37	(((heterojunction hetero) with (bipolar bi near polar) with	USPAT;	2003/10/10 11:42
		(transistor) hbt hbts) and base and emitter with mesa and	US-PGPUB;	
		base with (contact and electrode)) and (((gallium indium ga	EPO; JPO;	
		in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in	DERWENT; IBM_TDB	
1		sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga	1011_100	
		in as" "in ga as")) and		,
-	94	(base/andeningeniendes)386).		2003/10/10 11:42
ŀ		and (((gallium indium ga in) with (arsenic antimony as sb)	US-PGPUB;	
		(gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as	EPO; JPO;	
		sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga in as" "in ga as")) and	DERWENT; IBM_TDB	
		((438/47,94,172,191,235,312,313,314,315,317,320,for.286).		
-	57	((base and emitter and base with (contact and electrode))	USPAT;	2003/10/10 13:42
		and (((gallium indium ga in) with (arsenic antimony as sb)	US-PGPUB;	
		(gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as	EPO; JPO;	
		sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb	DERWENT; IBM_TDB	
		as" gainas ingaas "ga in as" "in ga as")) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).0		
		not ((((heterojunction hetero) with (bipolar bi near polar)	,020.///	
i i		with (transistor) hbt hbts) and base and emitter with mesa		
		and base with (contact and electrode)) and (((gallium		
	İ	indium ga in) with (arsenic antimony as sb) (gainassb "ga in		
		as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas		
		ingaas "ga in as" "in ga as")) and		
-	1443	(thas 8/4/7, that is not so that the control of the	CUSPAT;	2003/10/10 13:42
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM_TDB	
_	193	(base and emitter and base near (contact and electrode))	USPAT;	2003/10/10 15:09
		and base with ((gallium indium ga in) with (arsenic antimony	US-PGPUB;	, ,
		as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in	EPO; JPO;	
		ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb"	DERWENT;	
	25	in sb as" gainas ingaas "ga in as" "in ga as")) (heat\$3 anneal\$4) with base with remov\$3 near (hydrogen	IBM_TDB USPAT;	2003/10/10 15:09
-	25	(near\$3 anneai\$4) with base with remov\$3 hear (hydrogen   "h.sub.2")	US-PGPUB;	2003/10/10 13.03
		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/40/40 47 45
-	26	(heat\$3 anneal\$4) with base with (eliminate remov\$3) near	USPAT;	2003/10/10 15:10
1		(hydrogen "h.sub.2")	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	13	((heat\$3 anneal\$4) with base with (eliminate remov\$3) near	USPAT;	2003/10/13 13:10
		(hydrogen "h.sub.2")) and (438/\$6 257/\$6)	US-PGPUB;	
			EPO; JPO;	
	-		DERWENT; IBM_TDB	
_	1153	lattice near (matched matching matches match) with (MBE	USPAT;	2003/10/13 12:07
		MOMBE epitaxial epitaxy)	US-PGPUB;	' '
			EPO; JPO;	
			DERWENT;	
	<u></u>		IBM_TDB	

Search History 10/13/03 1:25:57 PM Page 3

i.				
-	645	(lattice near (matched matching matches match) with (MBE	USPAT;	2003/10/13 12:07
	1	MOMBE epitaxial epitaxy)) and (438/\$6 257/\$6)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1649	(438/47,94,172,191,235,312,313,314,315,317,320,for.286).C	CLESPAT;	2003/10/13 12:07
			US-PGPUB;	
		•	EPO; JPO;	
			DERWENT,	
			IBM_TDB	
-	58	((lattice near (matched matching matches match) with (MBE	USPAT;	2003/10/13 12:08
		MOMBE epitaxial epitaxy)) and (438/\$6 257/\$6)) and	US-PGPUB;	
		((438/47,94,172,191,235,312,313,314,315,317,320,for.286).	CELEO), JPO;	
			DERWENT;	
			IBM TDB	
-	33	emitter with ((INP "in p") with (algaas gaalas "al ga as" "ga	USPAT;	2003/10/13 13:04
		al as"))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			TRM TOR	